

April 1988 Revised July 1999

#### 74F189

# 64-Bit Random Access Memory with 3-STATE Outputs

### **General Description**

The F189 is a high-speed 64-bit RAM organized as a 16word by 4-bit array. Address inputs are buffered to minimize loading and are fully decoded on-chip. The outputs are 3-STATE and are in the high impedance state whenever the Chip Select (CS) input is HIGH. The outputs are active only in the Read mode and the output data is the complement of the stored data.

#### **Features**

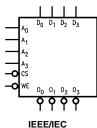
- 3-STATE outputs for data bus applications
- Buffered inputs minimize loading
- Address decoding on-chip
- Diode clamped inputs minimize ringing

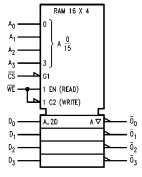
#### **Ordering Code:**

Order Number	Package Number	Package Description
74F189SC	M16B	16-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-013, 0.300" Wide
74F189SJ	M16D	16-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
74F189PC	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide

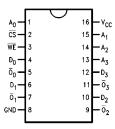
Devices also available in Tape and Reel. Specify by appending suffix "X" to the ordering code.

#### **Logic Symbols**





#### **Connection Diagram**



# **Unit Loading/Fan Out**

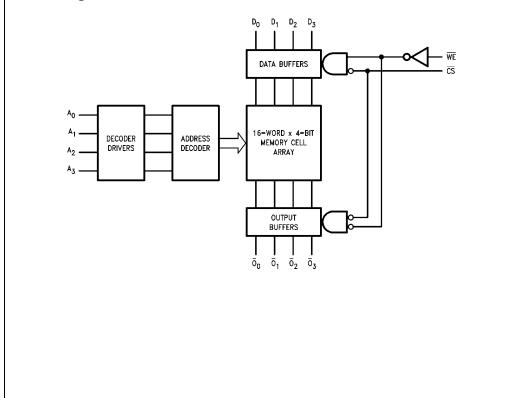
Pin Names	Decembrican	U.L.	Input I <sub>IH</sub> /I <sub>IL</sub>		
	Description	HIGH/LOW	Output I <sub>OH</sub> /I <sub>OL</sub>		
A <sub>0</sub> -A <sub>3</sub>	Address Inputs	1.0/1.0	20 μA/–0.6 mA		
CS	Chip Select Input (Active LOW)	1.0/1.0	20 μA/–1.2 mA		
WE	Write Enable Input (Active LOW)	1.0/1.0	20 μA/–0.6 mA		
D <sub>0</sub> -D <sub>3</sub>	Data Inputs	1.0/1.0	20 μA/–0.6 mA		
$\overline{O}_0 - \overline{O}_3$	Inverted Data Outputs	150/40 (33.3)	-3.0 mA/24 mA (20 mA)		

#### **Function Table**

Inputs		Onevetien	Condition of Outputs			
cs	WE	Operation	Condition of Outputs			
L	L	Write	High Impedance			
L	Н	Read	Complement of Stored Data			
Н	X	Inhibit	High Impedance			

H = HIGH Voltage Level L = LOW Voltage Level X = Immaterial

# **Block Diagram**



#### **Absolute Maximum Ratings**(Note 1)

-65°C to +150°C Storage Temperature Ambient Temperature under Bias  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ -55°C to +175°C Junction Temperature under Bias

V<sub>CC</sub> Pin Potential to

Ground Pin -0.5V to +7.0VInput Voltage (Note 2) -0.5V to +7.0VInput Current (Note 2)  $-30\ mA$  to  $+5.0\ mA$ 

Voltage Applied to Output

in HIGH State (with  $V_{CC} = 0V$ )

-0.5V to V<sub>CC</sub> Standard Output

3-STATE Output

Current Applied to Output in LOW State (Max)

#### **Recommended Operating Conditions**

Free Air Ambient Temperature 0°C to +70°C +4.5V to +5.5V Supply Voltage

**Note 1:** Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

 $-0.5V\ to\ +5.5V \qquad \text{Note 2: Either voltage limit or current limit is sufficient to protect inputs.}$ 

#### **DC Electrical Characteristics**

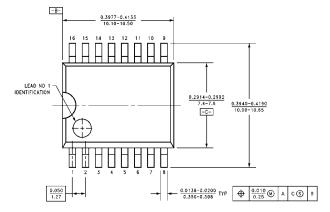
Symbol	I Parameter		Min	Min Typ Max		Units	v <sub>cc</sub>	Conditions		
V <sub>IH</sub>	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal		
V <sub>IL</sub>	Input LOW Voltage				8.0	V		Recognized as a LOW Signal		
V <sub>CD</sub>	Input Clamp Diode Volta	age			-1.2	V	Min	I <sub>IN</sub> = -18 mA		
V <sub>OH</sub>	Output HIGH	10% V <sub>CC</sub>	2.5					I <sub>OH</sub> = -1 mA		
	Voltage	10% V <sub>CC</sub>	2.4			v	Min	$I_{OH} = -3 \text{ mA}$		
		$5\%  \mathrm{V_{CC}}$	2.7			v v	IVIII	I <sub>OH</sub> = -1 mA		
		5% V <sub>CC</sub>	2.7					$I_{OH} = -3 \text{ mA}$		
V <sub>OL</sub>	Output LOW									
	Voltage	10% V <sub>CC</sub>			0.5	V	Min	I <sub>OL</sub> = 24 mA		
I <sub>IH</sub>	Input HIGH									
	Current				5.0	μΑ	Max	V <sub>IN</sub> = 2.7V		
I <sub>BVI</sub>	Input HIGH Current									
	Breakdown Test				7.0	μΑ	Max	V <sub>IN</sub> = 7.0V		
I <sub>CEX</sub>	Output HIGH									
	Leakage Current				50	μΑ	Max	$V_{OUT} = V_{CC}$		
V <sub>ID</sub>	Input Leakage		4.75			V	0.0	$I_{ID} = 1.9 \mu A$		
	Test							All Other Pins Grounded		
I <sub>OD</sub>	Output Leakage				3.75	μΑ	0.0	V <sub>IOD</sub> = 150 mV		
	Circuit Current							All Other Pins Grounded		
I <sub>IL</sub>	Input LOW Current				-0.6	mA	Max	V <sub>IN</sub> = 0.5V (except $\overline{\text{CS}}$ )		
					-1.2			V <sub>IN</sub> = 0.5V ( <del>CS</del> )		
I <sub>OZH</sub>	Output Leakage Curren	t			50	μА	Max	V <sub>OUT</sub> = 2.7V		
I <sub>OZL</sub>	Output Leakage Curren	t			-50	μА	Max	V <sub>OUT</sub> = 0.5V		
Ios	Output Short-Circuit Cu	rrent	-60		-150	mA	Max	V <sub>OUT</sub> = 0V		
I <sub>ZZ</sub>	Bus Drainage Test				500	μА	0.0V	V <sub>OUT</sub> = 5.25V		
I <sub>CCZ</sub>	Power Supply Current			37	55	mA	Max	V <sub>O</sub> = HIGH Z		

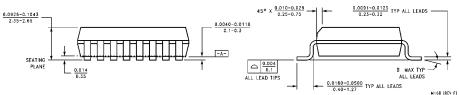
AC EI	ectrical Characteris	tics							
Symbol		$T_A = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_L = 50 \text{ pF}$			$T_{A} = -55^{\circ}C \text{ to } +125^{\circ}C$ $V_{CC} = +5.0V$ $C_{L} = 50 \text{ pF}$		$T_A = 0$ °C to +70°C $V_{CC} = +5.0V$ $C_L = 50 \text{ pF}$		Units
	Parameter								
		t <sub>PLH</sub>	Access Time, HIGH or LOW	10.0	18.5	26.0	9.0	32.0	10.0
t <sub>PHL</sub>	$A_n$ to $\overline{O}_n$	8.0	13.5	19.0	8.0	23.0	8.0	20.0	ns
t <sub>PZH</sub>	Access Time, HIGH or LOW	3.5	6.0	8.5	3.5	10.5	3.5	9.5	20
t <sub>PZL</sub>	CS to Ō <sub>n</sub>	5.0	9.0	13.0	5.0	15.0	5.0	14.0	ns
t <sub>PHZ</sub>	Disable Time, HIGH or LOW	2.0	4.0	6.0	2.0	8.0	2.0	7.0	20
t <sub>PLZ</sub>	CS to Ō <sub>n</sub>	3.0	5.5	8.0	2.5	10.0	3.0	9.0	ns
t <sub>PZH</sub>	Write Recovery Time,	6.5	15.0	28.0	6.5	37.5	6.5	29.0	
t <sub>PZL</sub>	HIGH or LOW $\overline{\text{WE}}$ to $\overline{\text{O}}_{\text{n}}$	6.5	11.0	15.5	6.5	17.5	6.5	16.5	ns
t <sub>PHZ</sub>	Disable Time, HIGH or LOW	4.0	7.0	10.0	3.5	12.0	4.0	11.0	20
t <sub>PLZ</sub>	WE to On	5.0	9.0	13.0	5.0	15.0	5.0	14.0	ns

# AC Operating Requirements

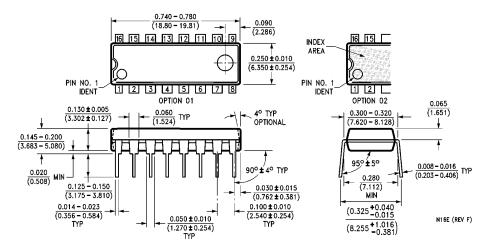
		$T_A = +25^{\circ}C$ $V_{CC} = +5.0V$		$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$		T <sub>A</sub> = 0°C to +70°C		
Symbol	Parameter			V <sub>CC</sub> =	+5.0V	$V_{CC} = +5.0V$		Units
		Min	Max	Min	Max	Min	Max	
t <sub>S</sub> (H)	Setup Time, HIGH or LOW	0		0		0		
$t_{S}(L)$	A <sub>n</sub> to WE	0		0		0		
t <sub>H</sub> (H)	Hold Time, HIGH or LOW	2.0		2.0		2.0		ns
$t_H(L)$	A <sub>n</sub> to WE	2.0		2.0		2.0		
t <sub>S</sub> (H)	Setup Time, HIGH or LOW	10.0		11.0		10.0		
$t_S(L)$	D <sub>n</sub> to WE	10.0		11.0		10.0		
t <sub>H</sub> (H)	Hold Time, HIGH or LOW	0		2.0		0		ns
t <sub>H</sub> (L)	D <sub>n</sub> to WE	0		2.0		0		
t <sub>S</sub> (L)	Setup Time, LOW	0		0		0		
	CS to WE							
t <sub>H</sub> (L)	Hold Time, LOW	6.0		7.5		6.0		ns
	CS to WE							
t <sub>W</sub> (L)	WE Pulse Width, LOW	6.0		15.0		6.0		ns

### Physical Dimensions inches (millimeters) unless otherwise noted

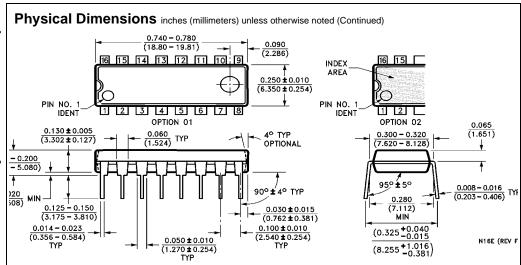




# 16-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS013, 0.300" Wide Body Package Number M16B



16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-OO1, 0.300" Wide Package Number N16E



16-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide Package Number M16D

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